

# Phase Control Thyristors (Hockey PUK Version), 1473 A



K-PUK (A-24)

PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	1473 A			
$V_{DRM}/V_{RRM}$	1200 V, 1400 V, 1600 V, 1800 V, 2000 V, 2200 V, 2400 V			
$V_{TM}$	1.80 V			
I <sub>GT</sub>	100 mA			
$T_J$	-40 °C to +125 °C			
Package	K-PUK (A-24)			
Circuit configuration	Single SCR			

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case K-PUK (A-24)
- High profile hockey PUK
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912">www.vishav.com/doc?99912</a>



## RoHS

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1473	A			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
1		2913	А			
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C			
I <sub>TSM</sub>	50 Hz	20.0	A			
	60 Hz	21.2				
l²t	50 Hz	2000	kA <sup>2</sup> s			
	60 Hz	1865				
I <sup>2</sup> √t		20 000	kA²√s			
V <sub>DRM</sub> /V <sub>RRM</sub>	Range	1200 to 2400	V			
tq	Typical	300	μs			
T <sub>J</sub>	Range	-40 to +125	°C			

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> MAXIMUM AT T <sub>J</sub> = 125 °C mA				
	12	1200	1300					
	14	1400	1500					
	16	1600	1700					
VS-ST1000CK	18	1800	1900	100				
	20	2000	2100					
	22	2200	2300					
	24	2400	2500					

Revision: 21-Sep-17 **1** Document Number: 93714



ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	I	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	I <sub>T(AV)</sub>	Double side	(single side) co	poled	55 (85)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	6540	Α
		t = 10 ms	No voltage		20.0	kA kA <sup>2</sup> s
Maximum peak, one-cycle,	<b>I</b>	t = 8.3 ms	reapplied		21.2	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	Sinusoidal half wave, initial $T_J = T_J$ maximum	17.0	
		t = 8.3 ms	reapplied		18.1	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage reapplied		2000	
		t = 8.3 ms			1865	
		t = 10 ms			1445	
		t = 8.3 ms	reapplied		1360	
Maximum $I^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1 ms to	t = 0.1 ms to 10 ms, no voltage reapplied			kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			]
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.283	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.265	11152
Maximum on-state voltage drop	$V_{TM}$	$I_{pk}$ = 3000 A, $T_J$ = 125 °C, $t_p$ = 10 ms sine pulse			1.80	V
Maximum holding current	I <sub>H</sub>	T _ 05 °C	T 0500 1 1 10V 111 1		600	mA
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load			1000	11114

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.9	
Typical turn-off time	t <sub>q</sub>	$I_{TM} = 550 \text{ A, } T_J = T_J \text{ maximum, dl/dt} = 40 \text{ A/}\mu\text{s,}$ $V_R = 50 \text{ V, dV/dt} = 20 \text{ V/}\mu\text{s, gate 0 V 100 }\Omega, t_p = 500 \mu\text{s}$	300	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA



TRIGGERING						
DADAMETER	CVMPOL	TTOT CONDITIONS		VALUES		
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS	
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum.	, t <sub>p</sub> ≤ 5 ms	16		w
Maximum peak average gate power	P <sub>G(AV)</sub>	$T_J = T_J \text{ maximum}$	, f = 50 Hz, d% = 50	(	3	7 VV
Maximum peak positive gate current	I <sub>GM</sub>			3	.0	Α
Maximum peak positive gate voltage	+V <sub>GM</sub>	$T_J = T_J \text{ maximum}$	$T_J = T_J$ maximum, $t_p \le 5$ ms			V
Maximum peak negative gate voltage	-V <sub>GM</sub>				.0	7
DC gate current required to trigger		T <sub>J</sub> = -40 °C	Maximum required gate trigger/	200	-	
	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		100	200	mA
	T <sub>J</sub> = 125 °C	50	-			
		T <sub>J</sub> = -40 °C	value which will trigger all units	1.4	-	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.1	3.0	V
		T <sub>J</sub> = 125 °C		0.9	-	
DC gate current not to trigger	I <sub>GD</sub>	T T manyimay ma	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J maximum$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.:	25	V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating temperature range	$T_{J}$		-40 to +125	°C		
Maximum storage temperature range	T <sub>Stg</sub>		-40 to +150			
Maximum thermal resistance,	В	DC operation single side cooled	0.042			
junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.021	K/W		
Maximum thermal resistance,	R <sub>thC-hs</sub>	DC operation single side cooled	0.006	IV VV		
case to heatsink		DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500	N		
Wedning force, ± 10 /0			(2500)	(kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet	K-PUK (A	-24)		

△R <sub>thJC</sub> CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR CONDUCTION		TEST COMPLETIONS	LIMITO	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.003	0.003	0.002	0.002	$T_J = T_J$ maximum		
120°	0.004	0.004	0.004	0.004			
90°	0.005	0.005	0.005	0.005		K/W	
60°	0.007	0.007	0.007	0.007			
30°	0.012	0.012	0.012	0.012			

#### Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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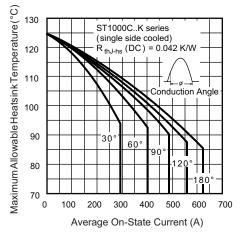


Fig. 1 - Current Ratings Characteristics

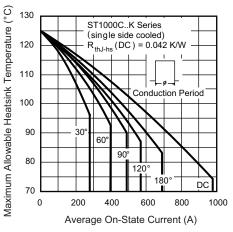


Fig. 2 - Current Ratings Characteristics

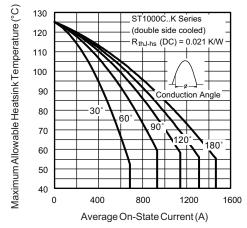


Fig. 3 - Current Ratings Characteristics

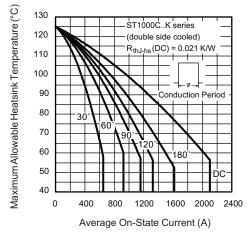


Fig. 4 - Current Ratings Characteristics

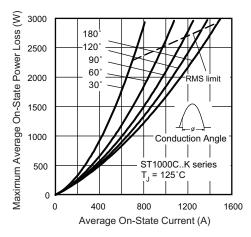


Fig. 5 - On-State Power Loss Characteristics

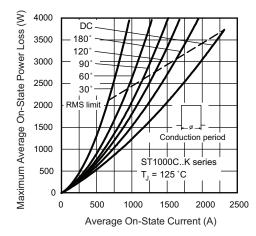


Fig. 6 - On-State Power Loss Characteristics



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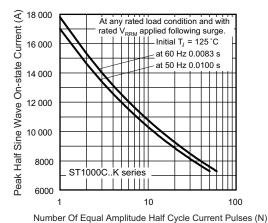


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

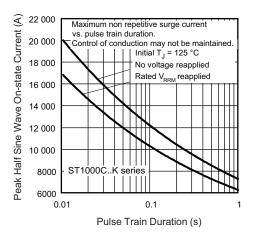


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

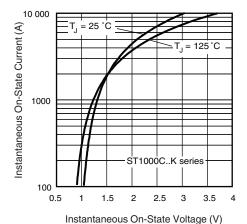


Fig. 9 - On-State Voltage Drop Characteristics

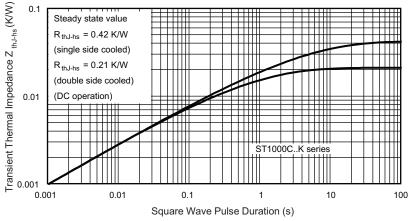


Fig. 10 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

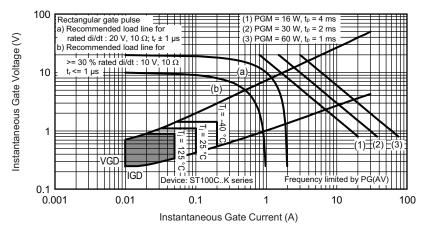
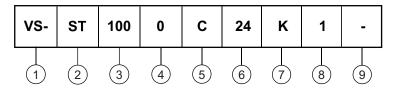


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**





1 - Vishay Semiconductors product

2 - Thyristor

Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - K = PUK case K-PUK (A-24)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • none = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

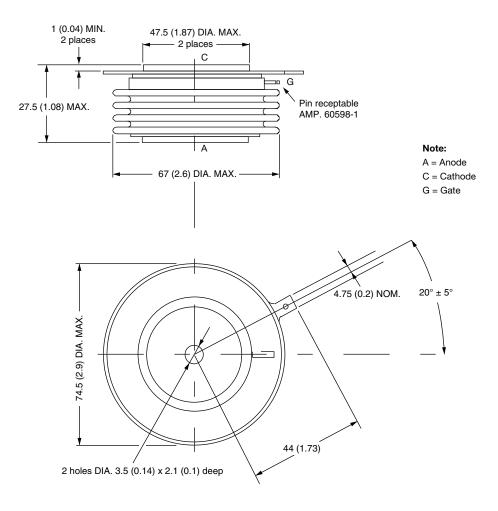
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95081		



# K-PUK (A-24)

### **DIMENSIONS** in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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